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(54) **EXTENDED SOURCE/DRAIN CONTACT FOR
SHIFTED DRAIN VOLTAGE FOR A
BACKSIDE POWER DISTRIBUTION
NETWORK**

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(57)

ABSTRACT

A semiconductor device includes at least a direct backside contact between a source line and a source epitaxial growth and/or a drain line and a drain epitaxial growth. A clock signal line contact via can connect a gate to a backside clock signal line. The clock signal line contact via is surrounded by a deep STI fill to prevent shorting between the clock signal line and the source and/or drain lines in the backside power rail.

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